



# NEC's NPN SiGe TRANSISTOR FOR LOW NOISE, HIGH -GAIN AMPLIFICATION

## NESG2046M33

### FEATURES

- **IDEAL FOR LOW NOISE, HIGH-GAIN AMPLIFICATION APPLICATIONS:**  
NF = 0.8 dB TYP.,  $G_a = 11.5$  dB TYP. @  $V_{CE} = 1$  V,  $I_c = 3$  mA,  $f = 2$  GHz
- **HIGH BREAKDOWN VOLTAGE TECHNOLOGY FOR SIGE TRANSISTORS :**  
 $V_{CEO}$  (absolute maximum ratings) = 5.0 V
- **3-PIN SUPER LEAD-LESS MINIMOLD (M33) PACKAGE**

### ORDERING INFORMATION

PART NUMBER	QUANTITY	SUPPLYING FORM
NESG2046M33-A	50 pcs (Non reel)	• 8 mm wide embossed taping
NESG2046M33-T3-A	10 kpcs/reel	• Pin 2 (Base) face the perforation side of the tape

**Remark** To order evaluation samples, contact your nearby sales office.  
The unit sample quantity is 50 pcs.

### ABSOLUTE MAXIMUM RATINGS ( $T_A = +25^\circ\text{C}$ )

PARAMETER	SYMBOL	RATINGS	UNIT
Collector to Base Voltage	$V_{CBO}$	13	V
Collector to Emitter Voltage	$V_{CEO}$	5	V
Emitter to Base Voltage	$V_{EBO}$	1.5	V
Collector Current	$I_c$	40	mA
Total Power Dissipation	$P_{tot}$ <sup>Note</sup>	130	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-65 to +150	$^\circ\text{C}$

**Note** Mounted on  $1.08 \text{ cm}^2 \times 1.0 \text{ mm}$  (t) glass epoxy PCB

**Caution** Observe precautions when handling because these devices are sensitive to electrostatic discharge.

**ELECTRICAL CHARACTERISTICS** ( $T_A = +25^\circ\text{C}$ )

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>DC Characteristics</b>						
Collector Cut-off Current	$I_{CBO}$	$V_{CB} = 5\text{ V}, I_E = 0\text{ mA}$	–	–	100	nA
Emitter Cut-off Current	$I_{EBO}$	$V_{EB} = 0.5\text{ V}, I_C = 0\text{ mA}$	–	–	100	nA
DC Current Gain	$h_{FE}$ <sup>Note 1</sup>	$V_{CE} = 1\text{ V}, I_C = 2\text{ mA}$	140	180	220	–
<b>RF Characteristics</b>						
Gain Bandwidth Product	$f_T$	$V_{CE} = 1\text{ V}, I_C = 15\text{ mA}, f = 2\text{ GHz}$	15	18	–	GHz
Insertion Power Gain	$ S_{21e} ^2$	$V_{CE} = 1\text{ V}, I_C = 15\text{ mA}, f = 2\text{ GHz}$	11	13	–	dB
Noise Figure	NF	$V_{CE} = 1\text{ V}, I_C = 3\text{ mA}, f = 2\text{ GHz},$ $Z_S = Z_{Sopt}, Z_L = Z_{Lopt}$	–	0.8	1.5	dB
Associated Gain	$G_a$	$V_{CE} = 1\text{ V}, I_C = 3\text{ mA}, f = 2\text{ GHz},$ $Z_S = Z_{Sopt}, Z_L = Z_{Lopt}$	9.5	11.5	–	dB
Reverse Transfer Capacitance	$C_{re}$ <sup>Note 2</sup>	$V_{CB} = 1\text{ V}, I_E = 0\text{ mA}, f = 1\text{ MHz}$	–	0.2	0.4	pF

**Notes 1.** Pulse measurement:  $PW \leq 350\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$

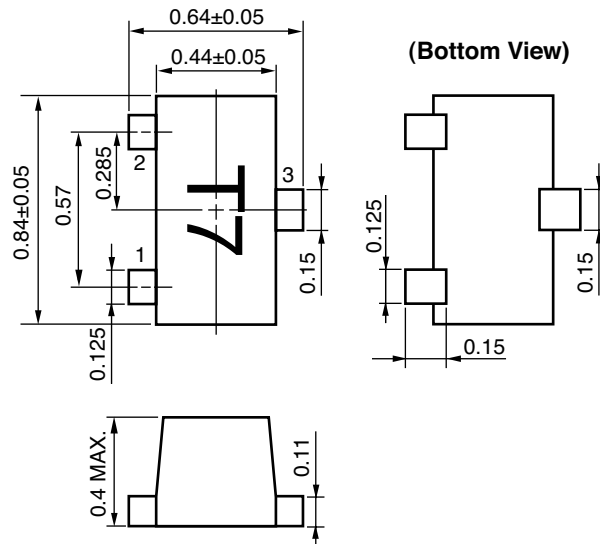
**2.** Collector to base capacitance when the emitter grounded

**h<sub>FE</sub> CLASSIFICATION**

RANK	FB
Marking	T7
$h_{FE}$ Value	140 to 220

## PACKAGE DIMENSIONS

### 3-PIN SUPER LEAD-LESS MINIMOLD (M33) (UNIT: mm)



### PIN CONNECTIONS

1. Emitter
2. Base
3. Collector

#### Life Support Applications

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

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DATA SUBJECT TO CHANGE WITHOUT NOTICE

09/09/2004

Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (\*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL’s understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration contained in CEL devices	
		-A	-AZ
Lead (Pb)	< 1000 PPM	Not Detected	(*)
Mercury	< 1000 PPM	Not Detected	
Cadmium	< 100 PPM	Not Detected	
Hexavalent Chromium	< 1000 PPM	Not Detected	
PBB	< 1000 PPM	Not Detected	
PBDE	< 1000 PPM	Not Detected	

If you should have any additional questions regarding our devices and compliance to environmental standards, please do not hesitate to contact your local representative.

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In no event shall CEL’s liability arising out of such information exceed the total purchase price of the CEL part(s) at issue sold by CEL to customer on an annual basis.

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